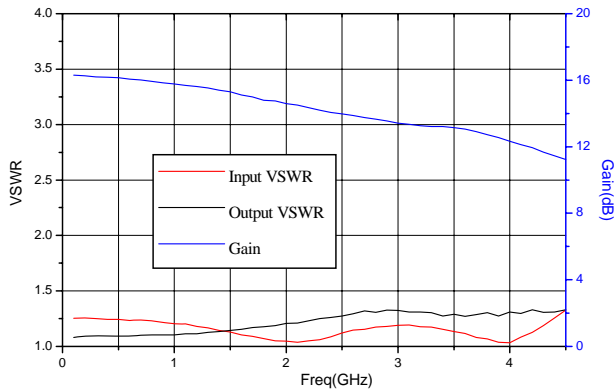


### Product Description

F220 is a high performance InGaP/GaAs Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration provides DC-4.5GHz performance with excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Only a single positive supply voltage, DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

F220 is RoHS compliant and manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.



**F220** RoHS Compliant & Green Package  
**DC—4500MHz, Cascadable InGaP/GaAs HBT MMIC Amplifier**



### Product Features

- Lead Free, RoHS Compliant
- High Gain:14.0dB @1950MHz
- Stable Gain Over Temperature
- 1000V ESD, Class 1C
- Operation from Single Supply
- Low Thermal Resistance

### Applications

- Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite Terminal

Symbol	Parameter	Units	Freq	Min.	Typ.	Max.
G	Small Signal Gain	dB	850MHz	14.1	15.5	17.3
			1950MHz		14.0	
			2400MHz		12.7	
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	850MHz 1950MHz		19.7 18.0	
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	850MHz 1950MHz		34.0 32.0	
Bandwidth	VSWR<2.0	MHz			4500	
Input VSWR	Input VSWR	Ratio	1950MHz		1.2	2.0
Output VSWR	Output VSWR	Ratio	1950MHz		1.2	2.0
NF	Noise Figure	dB	1950MHz		4.0	
V <sub>D</sub>	Device Operating Voltage	V		4.6	4.9	5.4
I <sub>D</sub>	Device Operating Current	mA		73	81	89
Test condition: V <sub>s</sub> =8V I <sub>D</sub> =81mA Typ OIP <sub>3</sub> Tone Spacing=1MHz, Pout per ton=5 dBm R <sub>BIAS</sub> =39 Ohms T <sub>L</sub> =25°C Z <sub>S</sub> =Z <sub>L</sub> =50 Ohms, App circuit page 4						

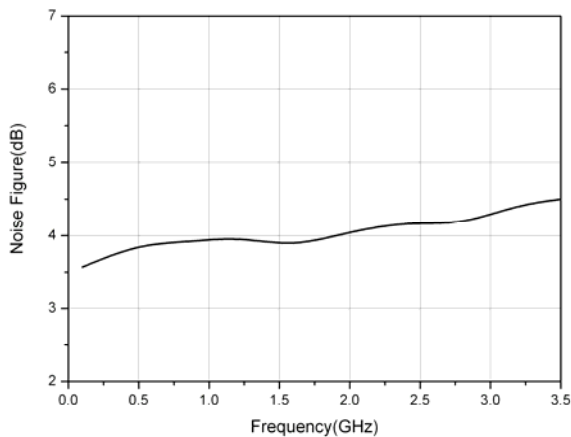
### Typical RF Performance at Key Operating Frequencies

symbol	parameter	units	Frequency (MHz)				
			100	500	850	1950	2400
G	Small Signal Gain	dB	16.0	15.8	15.5	14.0	12.7
OIP <sub>3</sub>		dBm	36.0	35.0	34.0	32.0	30.3
P <sub>1dB</sub>		dBm	19.5	19.8	19.7	18.0	17.3
Input VSWR			1.20	1.20	1.25	1.16	1.14
Output VSWR			1.08	1.08	1.11	1.17	1.16
S <sub>12</sub>	Reverse Isolation	dB	20.0	20.0	20.0	20.0	20.5
NF	Noise Figure	dB	4.0	3.8	3.9	4.0	4.3

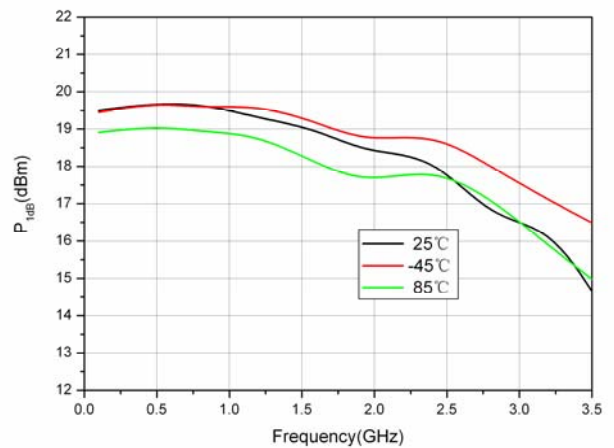
Test condition: V<sub>S</sub>=8V I<sub>D</sub>=81mA Typ R<sub>BIAS</sub>=39 Ohms T<sub>L</sub>=25°C Z<sub>S</sub>=Z<sub>L</sub>=50 Ohms,  
 OIP<sub>3</sub> Tone Spacing=1MHz, Pout per ton=5 dBm App circuit page 4

### Absolute Maximum Ratings

Parameters	Absolute Limit	Operation beyond any one of these limits may cause permanent damage. Bias Conditions should satisfy the following expression: $I_D V_D < (T_J - T_L) / R_{TH-j-1}$ $T_L = T_{LEAD}$
Max. Device Current (I <sub>D</sub> )	160 mA	
Max. Device Voltage(V <sub>D</sub> )	7V	
Max. RF Input Power	+18 dBm	
Max. Junction Temp. (T <sub>J</sub> )	+150°C	
Operating Temp. range (T <sub>L</sub> )	-40°C ~ +85°C	
Max. Storage Temp.	+150°C	

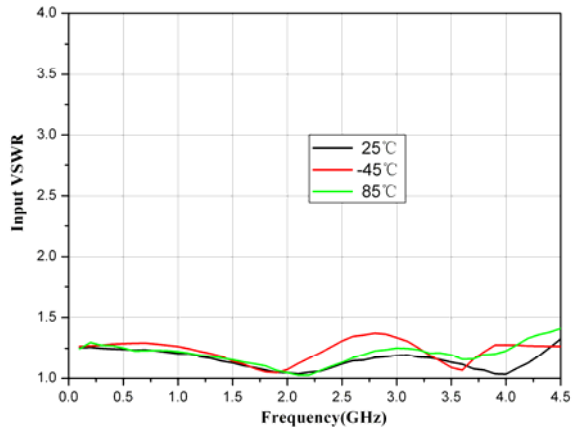


Noise figure vs. Frequency

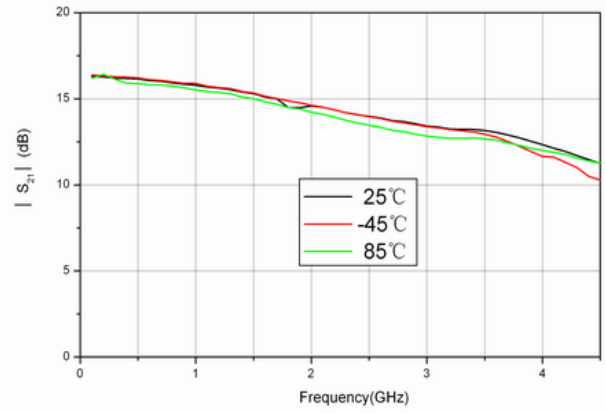


P<sub>1dB</sub> vs. Frequency

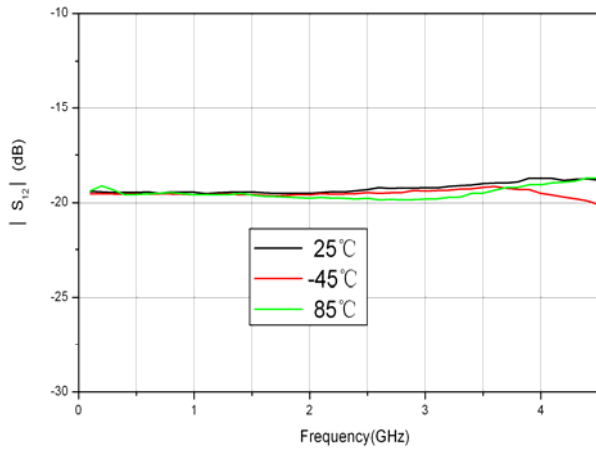
**Test Condition:  $V_s=8V$ ,  $R_{\text{bias}}=39\Omega$ ,  $I_d=81mA$**



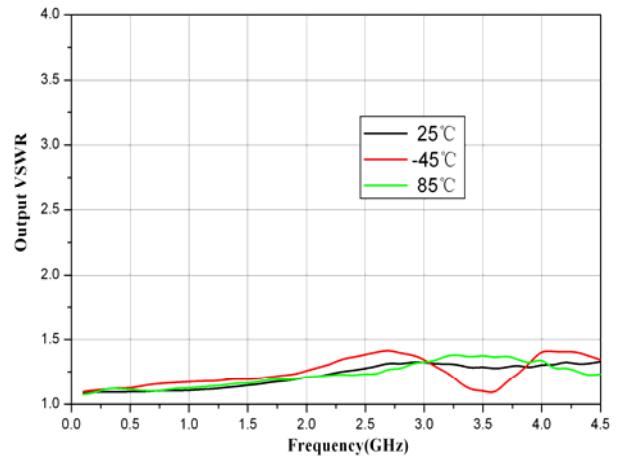
**Input VSWR vs. Frequency**



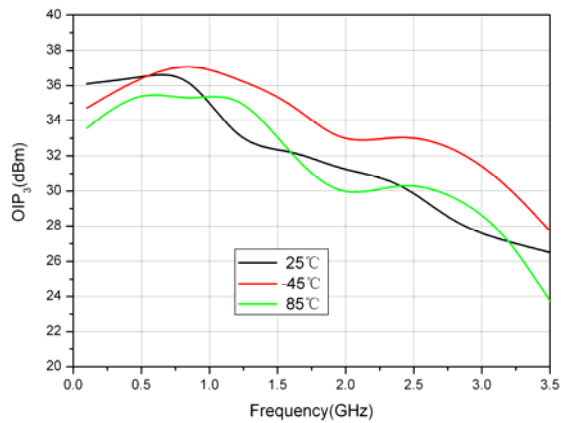
**S21 vs. Frequency**



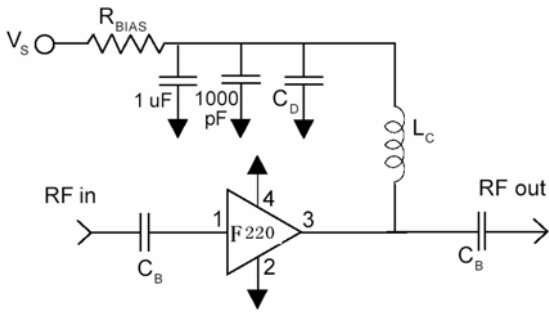
**S12 vs. Frequency**



**Output VSWR vs. Frequency**

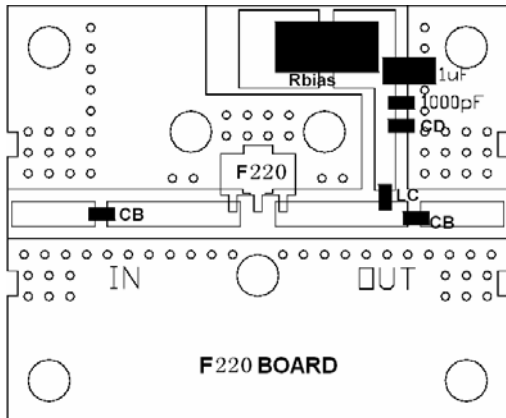


**OIP<sub>3</sub> vs. Frequency**



### Application Circuit Element Values

Reference Designator	Frequencies (MHz)				
	500	850	1950	2400	3500
C <sub>B</sub>	220pF	100pF	68 pF	56 pF	39pF
C <sub>D</sub>	100pF	68 pF	22 pF	22 pF	15 PF
L <sub>C</sub>	68 nH	33 nH	22 nH	18 nH	15 nH

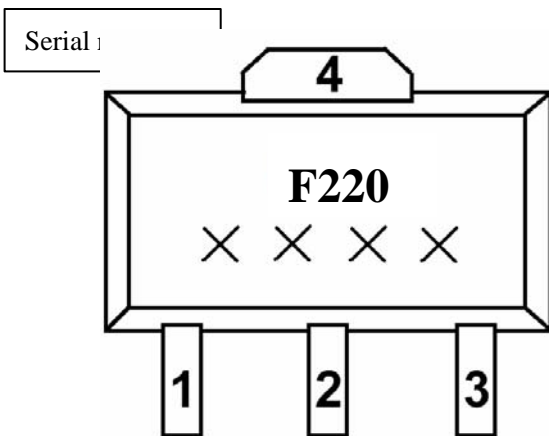


Supply voltage(V <sub>S</sub> )	Recommended Bias Resistor Value for I <sub>D</sub> =81mA			
	R <sub>BIAS</sub> =(V <sub>S</sub> - V <sub>D</sub> ) / I <sub>D</sub>			
6V	8V	10V	12V	
R <sub>BIAS</sub>	13 Ω	39 Ω	62 Ω	91 Ω

Note: R<sub>BIAS</sub> provides DC bias stability over Temp.

### Mounting Instructions

- NOTE: For broadband RF unconditional stability do not put GND vias under the exposed backside GND paddle.
- Solder the copper pad on the backside of the device package to the ground plane.
- Use a large ground pad area with many plated through-holes as shown.
- Measurement for this data sheet is made on 0.5 mm thick FR-4 board with 3.38 dielectric constant.



### Marking and Pin definition



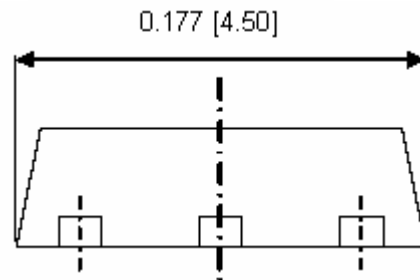
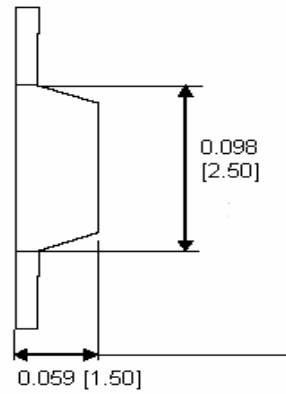
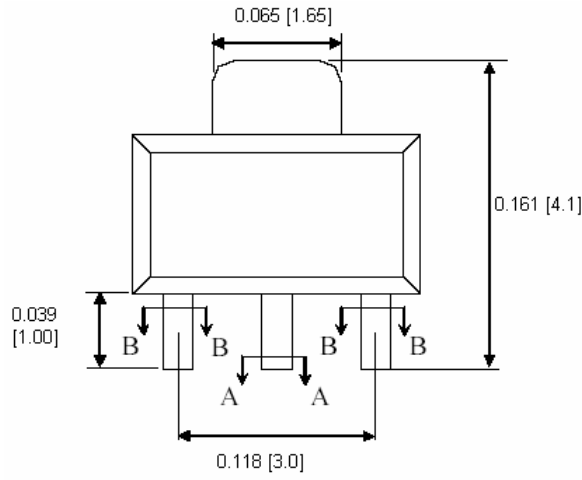
**ESD sensitive**

**Note: F220 must precaution in handing, testing and packaging !**

Pin	Function	Description
1	RF IN	RF input pin. This pin requires an external DC blocking capacitor.
2, 4	GND	Connecting to ground. Use via holes for best performance to reduce lead inductance.
3	RF OUT / BIAS	RF output and bias pin. DC blocking capacitor is necessary for proper operating.

SOT89 Packaging and PCB Pad Layout

Units: inch [millimeter]



Symbol	inch	millimeter
A	0.016	0.42
B	0.019	0.5

